

In the Specification:

Please replace the paragraph beginning on page 3, line 21 with the following rewritten paragraph:

C<sub>1</sub> --FIG. 2 includes SEM images of Pt-coated Si (100) after etching in HF/ H<sub>2</sub>O<sub>2</sub> for 30 s in accordance with the method of the invention. In each image, the top surface is tilted 30° from normal. FIG. 42(a) is an image of a Pt-coated area on p+ Si. FIG. 42(b) is an image taken off the Pt-coated area on p+ Si with an inset showing a high magnification view of the top surface. The scale bars represent 1.2 μm in FIGs. 2(a) and 2(b), respectively, while that of the inset represents 300 nm.--

Please replace the paragraph beginning on page 4, line 1 with the following rewritten paragraph:

C<sub>2</sub> --FIG. 3 includes top view SEM images of Pt-coated Si (100) after etching in HF/ H<sub>2</sub>O<sub>2</sub> for 30 s in accordance with the present invention. FIG. 43(a) is an image of a Pt-coated area of p- Si. FIG. 43-(b) is an image taken off the Pt coated area of p- Si.--